

<b>Notice of References Cited</b>		Application No. <b>08/691,434</b>		Applicant(s) <b>Yamazaki et al.</b>	
		Examiner <b>M. Wilczewski</b>		Group Art Unit <b>1107</b>	Page 1 of 1

  

U.S. PATENT DOCUMENTS						
*	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	
	A	5,304,357	4/1994	Sato et al.	---	---
	B	4,475,027	10/1984	Pressley	---	---
	C					
	D					
	E					
	F					
	G					
	H					
	I					
	J					
	K					
	L					
	M					

  

FOREIGN PATENT DOCUMENTS						
*	DOCUMENT NO.	DATE	COUNTRY	NAME	CLASS	SUBCLASS
X	N	3-286518	12/1991	JP	Hashizume	----
X	O	64-76715	3/1989	JP	Sera	----
X	P	2-73623	3/1990	JP	Aoyama et al.	----
	Q					
	R					
	S					
	T					

  

NON-PATENT DOCUMENTS		
*	DOCUMENT (Including Author, Title, Source, and Pertinent Pages)	DATE
X	U Wagner et al., Formation of p-n Junctions and Silicides in Silicon Using a High Performance Laser Beam Homogenization System, Applied Surface Science, Vol. 43, 1989, pp. 260-263.	1989
X	V Jhon et al., Crystallization of Amorphous Silicon by Excimer Laser Annealing With a Line Shape Beam Having a Gaussian Profile, Jpn. J. Appl. Phys., Vol. 33, 1994, pp. L 1438-L 1441, Part 2, No. 10B, 15 October 1994.	1994
	W	
	X	

\* A copy of this reference is not being furnished with this Office action.  
(See Manual of Patent Examining Procedure, Section 707.05(a).)